$0.9-\Omega$ SPDT ANALOG SWITCH 5-V/3.3-V SINGLE-CHANNEL 2:1 MULTIPLEXER/DEMULTIPLEXER

Check for Samples: TS5A3154

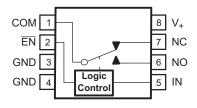
FEATURES

- · Specified Make-Before-Break Switching
- Low ON-State Resistance (0.9 Ω)
- Control Inputs Are 5.5-V Tolerant
- Low Charge Injection
- Excellent ON-State Resistance Matching
- · Low Total Harmonic Distortion (THD)
- 1.65-V to 5.5-V Single-Supply Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)

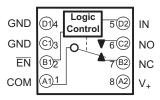
APPLICATIONS

- Cell Phones
- PDAs
- Portable Instrumentation
- Audio and Video Signal Routing
- Low-Voltage Data-Acquisition Systems
- Communication Circuits
- Modems
- Hard Drives
- Computer Peripherals
- Wireless Terminals and Peripherals

DCU PACKAGE (TOP VIEW)



YZP PACKAGE (BOTTOM VIEW)



DESCRIPTION/ORDERING INFORMATION

The TS5A3154 is a single-pole double-throw (SPDT) analog switch that is designed to operate from 1.65 V to 5.5 V. The device offers a low ON-state resistance and an excellent channel-to-channel ON-state resistance matching. The device has excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

Table 1. ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾ (2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING (3)
–40°C to 85°C	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Reel of 3000	TS5A3154YZPR	JX_
	SSOP - DCU	Reel of 3000	TS5A3154DCUR	JCF_

- (1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
- (2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
- (3) DCU: The actual top-side marking has one additional character that designates the assembly/test site.

 YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, = Pb-free).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NanoFree is a trademark of Texas Instruments.



Table 2. FUNCTION TABLE

EN	IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	L	ON	OFF
L	Н	OFF	ON
Н	X	OFF	OFF

Table 3. Summary of Characteristics⁽¹⁾

Configuration	Single-Pole, Double-Throw 2:1 Multiplexer/Demultiplexer (SPDT)
Number of channels	1
ON-state resistance (r _{on})	0.9 Ω
ON-state resistance match (Δr _{on})	0.1 Ω
ON-state resistance flatness (r _{on(flat)})	0.15 Ω
Turn-on/turn-off time (t _{ON} /t _{OFF})	8 ns/12.5 ns
Make-before-break time (t _{MBB})	12 ns
Charge injection (Q _C)	10 pC
Bandwidth (BW)	100 MHz
OFF isolation (O _{ISO})	-64 dB at 1 MHz
Crosstalk (X _{TALK})	-64 dB at 1 MHz
Total harmonic distortion (THD)	0.004%
Leakage current (I _{COM(OFF)} /I _{NC(OFF)})	±20 nA
Power-supply current (I ₊)	0.1 μΑ
Package option	8-pin SSOP or DSBGA

(1) $V_+ = 5 \text{ V}, T_A = 25^{\circ}\text{C}$

Absolute Minimum and Maximum Ratings⁽¹⁾ (2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V ₊	Supply voltage range ⁽³⁾		-0.5	6.5	V
V_{NC}, V_{NO}, V_{COM}	Analog voltage range ⁽³⁾ (4) (5)		-0.5	V ₊ + 0.5	V
I_{K}	Analog port diode current	V_{NC} , V_{NO} , $V_{COM} < 0$ or V_{NO} , V_{NC} , $V_{COM} > V_{+}$	-50	50	mA
I _{NC} ,	On-state switch current		-200	200	
I _{COM} , I _{NO}	On-state peak switch current ⁽⁶⁾	V_{NC} , V_{NO} , $V_{COM} = 0$ to V_{+}	-400	400	mA
V_{I}	Digital input voltage range (3) (4)		-0.5	6.5	V
I _{IK}	Digital input clamp current	V ₁ < 0	-50		mA
I ₊	Continuous current through V+	•		100	mA
I _{GND}	Continuous current through GND		-100	100	mA
0	Declines the survey lines and are as (7)	DCU package		227	°C/M
θ_{JA}	Package thermal impedance (7)	YZP package		102	°C/W
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

Product Folder Link(s): TS5A3154

⁽²⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

³⁾ All voltages are with respect to ground, unless otherwise specified.

⁽⁴⁾ The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

⁽⁵⁾ This value is limited to 5.5 V maximum.

⁶⁾ Pulse at 1-ms duration < 10% duty cycle.

⁽⁷⁾ The package thermal impedance is calculated in accordance with JESD 51-7.



Electrical Characteristics for 5-V Supply⁽¹⁾

 $V_{+} = 4.5 \text{ V}$ to 5.5 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Analog Switch	1	T.		•					
Analog signal range	V _{COM} , V _{NO} , V _{NC}					0		V ₊	V
Peak ON resistance	r _{peak}	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 13	25°C Full	4.5 V		0.9	1.1	Ω
ON-state resistance	r _{on}	V_{NO} or $V_{NC} = 2.5 \text{ V}$, $I_{COM} = -100 \text{ mA}$,	Switch ON, See Figure 13	25°C Full	4.5 V		0.8	0.9	Ω
ON-state				25°C			0.05	0.1	
resistance matching between channels	Δr _{on}	V_{NO} or $V_{NC} = 2.5 \text{ V}$, $I_{COM} = -100 \text{ mA}$,	Switch ON, See Figure 13	Full	4.5 V		0.00	0.1	Ω
		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C			0.15		
ON-state		$I_{COM} = -100 \text{ mA},$	See Figure 13	Full					_
resistance flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 1 \text{ V}, 1.5 \text{ V},$	Switch ON,	25°C	4.5 V		0.09	0.15	Ω
natricss		$I_{COM} = -100 \text{ mA},$	See Figure 13	Full				0.15	
		V_{NC} or $V_{NO} = 1 V$,		25°C		-20	2	20	
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	$V_{COM} = 4.5 \text{ V},$ or V_{NC} or $V_{NO} = 4.5 \text{ V},$ $V_{COM} = 1 \text{ V},$	Switch OFF, See Figure 14	Full	5.5 V	-150		150	nA
Carrent	I _{NC(PWROFF)} ,	V_{NC} or $V_{NO} = 0$ to 5.5 V,	Switch OFF,	25°C	0.1/	– 5	0.7	5	
	I _{NO(PWROFF)}	$V_{COM} = 5.5 \text{ V to } 0,$	See Figure 14	Full	0 V	-25		25	μA
		V_{NC} or $V_{NO} = 1 V$,		25°C		-20	2	20	
NC, NO ON leakage current	I _{NC(ON)} , I _{NO(ON)}	$V_{COM} = Open,$ or V_{NC} or $V_{NO} = 4.5 \text{ V},$ $V_{COM} = Open,$	Switch ON, See Figure 15	Full	5.5 V	-150		150	nA
		$V_{COM} = 1 V, V_{NC} or$		25°C		-20	2	20	
COM OFF leakage current	I _{COM(OFF)}	$V_{NO} = 4.5 \text{ V},$ or $V_{COM} = 4.5 \text{ V},$ $V_{NC} \text{ or } V_{NO} = 1 \text{ V},$	Switch OFF, See Figure 14	Full	5.5 V	-150		150	nA
dancin		V_{NC} or $V_{NO} = 0$ to 5.5 V,	Switch OFF,	25°C	0.1/	– 5	0.7	5	
	I _{COM(PWROFF)}	$V_{COM} = 5.5 \text{ V to } 0,$	See Figure 14	Full	0 V	-25		25	μA
		$V_{COM} = 1 V$,		25°C		-20	2	20	
COM ON leakage current	I _{COM(ON)}	V_{NC} or V_{NO} = Open, or V_{COM} = 4.5 V, V_{NC} or V_{NO} = Open,	Switch ON, See Figure 15	Full	5.5 V	-150		150	nA
Digital Control In	nputs (IN, EN) ⁽²⁾								
Input logic high	V _{IH}			Full		2.4		5.5	V
				E				0.0	V
Input logic low	V_{IL}			Full		0		0.8	V

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum. All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

Electrical Characteristics for 5-V Supply⁽¹⁾ (continued)

 $V_{+} = 4.5 \text{ V}$ to 5.5 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONI	DITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Dynamic								'!	
Turn or time			0 25 - 5	25°C	5 V	1	5.2	8	
Turn-on time, IN or OE	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 17	Full	4.5 V to 5.5 V	1		9	ns
Turn-off time,		V V	$C_1 = 35 pF$,	25°C	5 V	5	9.5	12.5	
IN or OE	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 17	Full	4.5 V to 5.5 V	4		13.5	ns
Make-before-		\/ - \/	$C_1 = 35 \text{ pF},$	25°C	5 V	4	6.3	12	
break time	t _{MBB}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 18	Full	4.5 V to 5.5 V	4		13	ns
Charge injection	$Q_{\mathbb{C}}$	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 22	25°C	5 V		10		pC
NC, NO OFF capacitance	$\begin{matrix} C_{NC(OFF)}, \\ C_{NO(OFF)} \end{matrix}$	V_{NC} or $V_{NO} = V_{+}$ or GND,	Switch OFF, See Figure 16	25°C	5 V		19		pF
NC, NO ON capacitance	$C_{NC(ON)}, \ C_{NO(ON)}$	V_{NC} or $V_{NO} = V_{+}$ or GND,	Switch ON, See Figure 16	25°C	5 V		57		pF
COM OFF capacitance	$C_{\text{COM(OFF)}}$	$V_{COM} = V_{+} \text{ or GND},$	Switch ON, See Figure 16	25°C	5 V		36		pF
COM ON capacitance	C _{COM(ON)}	$V_{COM} = V_{+}$ or GND,	Switch ON, See Figure 16	25°C	5 V		57		pF
Digital input capacitance	C_{l}	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	5 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$,	Switch ON, See Figure 19	25°C	5 V		100		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, See Figure 20	25°C	5 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 21	25°C	5 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	5 V		0.004		%
Supply				•					
Positive supply current	l ₊	$V_1 = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	5.5 V		0.02	0.1 0.5	μΑ

Copyright © 2005–2012, Texas Instruments Incorporated



Electrical Characteristics for 3.3-V Supply⁽¹⁾

 $V_{+} = 3 \text{ V}$ to 3.6 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIO	NS	TA	V+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	$V_{\mbox{COM}}, V_{\mbox{NO}}, V_{\mbox{NC}}$					0		V ₊	V
Peak ON resistance	r _{peak}	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 13	25°C Full	3 V		1.3	1.6 1.9	Ω
ON-state resistance	r _{on}	V_{NO} or $V_{NC} = 2 \text{ V}$, $I_{COM} = -100 \text{ mA}$,	Switch ON, See Figure 13	25°C	3 V		1.2	1.5	Ω
ON-state		ICOM = -100 IIIA,	Occ riguic 13	Full 25°C			0.08	1.7 0.15	
resistance match between channels	Δr_{on}	V_{NO} or $V_{NC} = 2$ V, 0.8 V $I_{COM} = -100$ mA,	Switch ON, See Figure 13	Full	3 V			0.15	Ω
ONI atata		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C			0.3		
ON-state resistance	r _{on(flat)}	$I_{COM} = -100 \text{ mA},$	See Figure 13	Full 25°C	3 V		0.09	0.15	Ω
flatness		V_{NO} or $V_{NC} = 2 \text{ V}$, 0.8 V, $I_{COM} = -100 \text{ mA}$,	Switch ON, See Figure 13	Full			0.03	0.15	
	I _{NC(OFF)} ,	V_{NC} or $V_{NO} = 1 \text{ V}$, $V_{COM} = 3 \text{ V}$,	Switch OFF,	25°C		-20	2	20	
NC, NO OFF leakage	I _{NO(OFF)}	or V_{NC} or $V_{NO} = 3 \text{ V}$, $V_{COM} = 1 \text{ V}$,	See Figure 14	Full	3.6 V	– 50		50	nA
current	I _{NC(PWROFF)} , I _{NO(PWROFF)}	V_{NC} or $V_{NO} = 0$ to 3.6 V, $V_{COM} = 3.6$ V to 0 V,	Switch OFF, See Figure 14	25°C	0 V	-1 45	0.2	1	μΑ
NC, NO	'NO(PWROFF)	V_{NC} or $V_{NO} = 1$ V, $V_{COM} = Open$,		Full 25°C		-15 -20	2	15 20	
ON leakage current	I _{NC(ON)} , I _{NO(ON)}	or V_{NC} or $V_{NO} = 3$ V, $V_{COM} = Open$,	Switch ON, See Figure 15	Full	3.6 V	-50		50	nA
	1	$V_{COM} = 1 \text{ V}, V_{NC} \text{ or } V_{NO} = 3 \text{ V},$	Switch OFF,	25°C	3.6 V	-20	2	20	nA
COM OFF leakage	I _{COM(OFF)}	or $V_{COM} = 3 \text{ V}, V_{NC} \text{ or } V_{NO} = 1 \text{ V},$	See Figure 14	Full	3.0 V	– 50		50	IIA
current	I _{COM(PWROFF)}	V_{NC} or $V_{NO} = 0$ to 3.6 V,	Switch OFF,	25°C	0 V	-1	0.2	1	μΑ
COM		$V_{COM} = 3.6 \text{ V to } 0,$ $V_{COM} = 1 \text{ V}, V_{NC} \text{ or } V_{NO} = \text{Open},$	See Figure 14	Full 25°C		-15 -20	2	15 20	
ON leakage current	I _{COM(ON)}	$v_{COM} = 1 \text{ V}, v_{NC} \text{ or } v_{NO} = \text{Open},$ or $v_{COM} = 3 \text{ V}, v_{NC} \text{ or } v_{NO} = \text{Open}$	Switch ON, See Figure 15	Full	3.6 V	-50		50	nA
Digital Control I	nputs (IN, EN) ⁽²⁾					· 		'	
Input logic high	V _{IH}			Full		2	-	5.5	V
Input logic low	V_{IL}			Full		0		8.0	V
Input leakage current	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C Full	3.6 V	-100 -100	25	100 100	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

Electrical Characteristics for 3.3-V Supply⁽¹⁾ (continued)

 $V_{+} = 3 \text{ V to } 3.6 \text{ V}, T_{A} = -40 ^{\circ}\text{C} \text{ to } 85 ^{\circ}\text{C} \text{ (unless otherwise noted)}$

PARAMETER	SYMBOL	TEST CONDI	ITIONS	T _A	V+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time,		V - V	$C_1 = 35 \text{ pF},$	25°C	3.3 V	3	6	10	
IN or OE	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 17	Full	3 V to 3.6 V	2		10.5	ns
Turn-off time.		$V_{COM} = V_+,$	$C_1 = 35 \text{ pF},$	25°C	3.3 V	5	10	15	
IN or OE	t_{OFF}	$R_L = 50 \Omega,$	See Figure 17	Full	3 V to 3.6 V	4		17	ns
Make-before-		$V_{COM} = V_+,$	$C_L = 35 \text{ pF},$	25°C	3.3 V	4	5.7	12	
break time	t _{MBB}	$R_L = 50 \Omega,$	See Figure 18	Full	3 V to 3.6 V	4		13	ns
Charge injection	$Q_{\mathbb{C}}$	$V_{GEN} = 0,$ $R_{GEN} = 0,$	$C_L = 1 \text{ nF},$ See Figure 22	25°C	3.3 V		9		pC
NC, NO OFF capacitance	$C_{NC(OFF)}, \ C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_{+}$ or GND,	Switch OFF, See Figure 16	25°C	3.3 V		19		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND,	Switch ON, See Figure 16	25°C	3.3 V		57		pF
COM OFF capacitance	C _{COM(OFF)}	V _{COM} = V ₊ or GND,	Switch ON, See	25°C	3.3 V		36		pF
COM ON capacitance	C _{COM(ON)}	$V_{COM} = V_{+} \text{ or GND},$	Switch ON, See Figure 16	25°C	3.3 V		57		pF
Digital input capacitance	C _I	$V_1 = V_+ \text{ or GND},$	See Figure 16	25°C	3.3 V		2		pF
Bandwidth	BW	R _L = 50 Ω,	Switch ON, See Figure 19	25°C	3.3 V		100		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch OFF, See Figure 20	25°C	3.3 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch ON, See Figure 21	25°C	3.3 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	3.3 V		0.01		%
Supply									
Positive supply current	I ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	3.6 V		0.01	0.1	μA



Electrical Characteristics for 2.5-V Supply⁽¹⁾

 $V_{+} = 3 \text{ V}$ to 3.6 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	DITIONS	T _A	V,	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	$V_{\rm COM},V_{\rm NO},$					0		V ₊	V
Peak ON resistance	r _{peak}	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -8 \text{ mA},$	Switch ON, See Figure 13	25°C Full	2.3 V		1.9	2.5 2.7	Ω
ON-state resistance	r _{on}	V_{NO} or $V_{NC} = 1.8 \text{ V}$, $I_{COM} = -8 \text{ mA}$,	Switch ON, See Figure 13	25°C Full	2.3 V		1.6	2.1 2.5	Ω
ON-state		, , , , , , , , , , , , , , , , , , ,		25°C			0.12	0.2	
resistance matching between channels	Δr_{on}	V_{NO} or $V_{NC} = 1.8 \text{ V}$, $I_{COM} = -8 \text{ mA}$,	Switch ON, See Figure 13	Full	2.3 V		0.12	0.2	Ω
		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C			0.65		
ON-state resistance	r	$I_{COM} = -8 \text{ mA},$	See Figure 13	Full	2.3 V				Ω
flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 0.8 \text{ V}$, 1.8 V,	Switch ON,	25°C	2.3 V		0.5	1	. 12
		$I_{COM} = -8 \text{ mA},$	See Figure 13	Full				1	
		V_{NC} or $V_{NO} = 0.5 \text{ V}$,		25°C		-20	2	20	
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	$V_{COM} = 2.3 \text{ V},$ or V_{NC} or $V_{NO} = 2.3 \text{ V},$ $V_{COM} = 0.5 \text{ V},$	Switch OFF, See Figure 14	Full	2.7 V	- 50		50	nA
	I _{NC(PWROFF)} ,	V_{NC} or $V_{NO} = 0$ to 2.7 V,	Switch OFF,	25°C	0 V	-1		1	
	I _{NO(PWROFF)}	$V_{COM} = 2.7 \text{ V to } 0,$	See Figure 14	Full	υv	-10		10	μA
		V_{NC} or $V_{NO} = 0.5 \text{ V}$,		25°C		-20		20	
NC, NO ON leakage current	I _{NC(ON)} , I _{NO(ON)}	$V_{COM} = Open,$ or V_{NC} or $V_{NO} = 2.3 \text{ V},$ $V_{COM} = Open,$	Switch ON, See Figure 15	Full	2.7 V	- 50		50	nA
		$V_{COM} = 0.5 \text{ V}, V_{NC} \text{ or}$		25°C		-20		20	
COM OFF leakage current	I _{COM(OFF)}	$\begin{split} &V_{NO}=2.3 \text{ V},\\ &\text{or}\\ &V_{COM}=2.3 \text{ V}, V_{NC} \text{ or}\\ &V_{NO}=0.5 \text{V}, \end{split}$	Switch OFF, See Figure 14	Full	2.7 V	– 50		50	nA
ourion	I _{COM(PWROFF)}	V_{NC} or $V_{NO} = 0$ to 2.7 V, $V_{COM} = 2.7$ V to 0,	Switch OFF, See Figure 14	25°C Full	0 V	-1 -10		1 10	μΑ
		$V_{COM} = 0.5 \text{ V}, V_{NC} \text{ or}$		25°C		-20		20	
COM ON leakage current	I _{COM(ON)}	V_{NO} = Open, or V_{COM} = 2.3 V, V_{NC} or V_{NO} = Open,	Switch ON, See Figure 15	Full	2.7 V	-50		50	nA
Digital Control Ir	nputs (IN, EN) ⁽²⁾								
Input logic high	V_{IH}			Full		1.8		5.5	V
Input logic low	V _{IL}			Full		0		0.6	V
Input leakage current	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C Full	2.7 V	-100 -100	25	100 100	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

Electrical Characteristics for 2.5-V Supply⁽¹⁾ (continued)

 $V_{+} = 3 \text{ V to } 3.6 \text{ V}, T_{A} = -40^{\circ}\text{C to } 85^{\circ}\text{C} \text{ (unless otherwise noted)}$

PARAMETER	SYMBOL	TEST CONI	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic								·	
Turn-on time.		V - V	$C_1 = 35 pF$	25°C	2.5 V	4	7.0	11.5	
IN or OE	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 17	Full	2.3 V to 2.7 V	3.5		12	ns
Turn-off time,		V	$C_{L} = 35 \text{ pF},$	25°C	2.5 V	5	11.5	18.5	
IN or OE	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 17	Full	2.3 V to 2.7 V	4		21	ns
Make-before-		$V_{COM} = V_+,$	$C_1 = 35 \text{ pF},$	25°C	2.5 V	4	6.3	15	
break time	t _{MBB}	$R_L = 50 \Omega,$	See Figure 18	Full	2.3 V to 2.7 V	4		16	ns
Charge injection	$Q_{\mathbb{C}}$	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 22	25°C	2.5 V		7		рС
NC, NO OFF capacitance	$\begin{matrix} C_{NC(OFF)}, \\ C_{NO(OFF)} \end{matrix}$	V_{NC} or $V_{NO} = V_{+}$ or GND,	Switch OFF, See Figure 16	25°C	2.5 V		19		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND,	Switch ON, See Figure 16	25°C	2.5 V		57		pF
COM OFF capacitance	C _{COM(OFF)}	V _{COM} = V ₊ or GND,	Switch ON, See Figure 16	25°C	2.5 V		36		pF
COM ON capacitance	C _{COM(ON)}	$V_{COM} = V_{+} \text{ or GND},$	Switch ON, See Figure 16	25°C	2.5 V		57		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	2.5 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$,	Switch ON, See Figure 19	25°C	2.5 V		100		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch OFF, See Figure 20	25°C	2.5 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch ON, See Figure 21	25°C	2.5 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	2.5 V		0.020		%
Supply									
Positive supply current	I ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	2.7 V		0.001	0.05 0.15	μΑ



Electrical Characteristics for 1.8-V Supply⁽¹⁾

 V_{+} = 1.65 V to 1.95 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	ITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	V
Peak ON resistance	r _{peak}	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 13	25°C Full	1.65 V		5.5	25 30	Ω
ON-state resistance	r _{on}	V_{NO} or $V_{NC} = 1.5 \text{ V}$, $I_{COM} = -2 \text{ mA}$,	Switch ON, See Figure 13	25°C	1.65 V		2	2.7	Ω
ON-state		COM – Z III I,	Cooringato to	Full 25°C			0.16	3.1 0.3	
resistance matching between channels	Δr_{on}	V_{NO} or $V_{NC} = 1.5 \text{ V}$, $I_{COM} = -2 \text{ mA}$,	Switch ON, See Figure 13	Full	1.65 V		0.10	0.3	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 13	25°C			3		
resistance flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 0.6 \text{ V}$, 1.5 V,	Switch ON,	25°C	1.65 V		3	20	Ω
		$I_{COM} = -2 \text{ mA},$	See Figure 13	Full				25	
		V_{NC} or $V_{NO} = 0.3 \text{ V}$,		25°C		-20	1.5	20	
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	$V_{COM} = 1.65 \text{ V},$ or $V_{NC} \text{ or } V_{NO} = 1.65 \text{ V},$ $V_{COM} = 0.3 \text{ V},$	Switch OFF, See Figure 14	Full	1.95 V	– 50		50	nA
odironi	I _{NC(PWROFF)} , I _{NO(PWROFF)}	V_{NC} or $V_{NO} = 0$ to 1.95 V, $V_{COM} = 1.95$ V to 0,	Switch OFF, See Figure 14	25°C Full	0 V	-1 -10	0.1	10	μΑ
		V_{NC} or $V_{NO} = 0.3 \text{ V}$,		25°C		-20	1.5	20	
NC, NO ON leakage current	I _{NC(ON)} , I _{NO(ON)}	$V_{COM} = Open,$ or V_{NC} or $V_{NO} = 1.65 V,$ $V_{COM} = Open,$	Switch ON, See Figure 15	Full	1.95 V	– 50		50	nA
		V_{NC} or $V_{NO} = 1.65 \text{ V}$,		25°C		-20	1.5	20	
COM OFF leakage current	I _{COM(OFF)}	$V_{COM} = 0.3 \text{ V},$ or $V_{NC} \text{ or } V_{NO} = 0.3 \text{ V},$ $V_{COM} = 1.65 \text{ V},$	Switch OFF, See Figure 14	Full	1.95 V	– 50		50	nA
	l	V_{NC} or $V_{NO} = 1.95 \text{ V to } 0$,	Switch OFF,	25°C	0 V	-1	0.06	1	μΑ
	ICOM(PWROFF)	$V_{COM} = 0 \text{ to } 1.95 \text{ V},$	See Figure 14	Full	0 0	-10		10	μΛ
СОМ		V_{NC} or V_{NO} = Open,		25°C		-20	1.5	20	
ON leakage current	I _{COM(ON)}	$V_{COM} = 0.3 \text{ V},$ or V_{NC} or $V_{NO} = \text{Open},$ $V_{COM} = 1.65 \text{ V},$	Switch ON, See Figure 15	Full	1.95 V	– 50		50	nA
Digital Control	Inputs (IN, EN)(2))		_					
Input logic high	V_{IH}			Full		1.5		5.6	V
Input logic low	V_{IL}			Full		0		0.6	V
Input leakage current	I_{lH} , I_{lL}	V _I = 5.5 V or 0		25°C Full	1.95 V	-100 -100	25	100	nA

¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₁ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

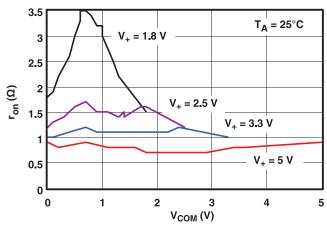
Electrical Characteristics for 1.8-V Supply⁽¹⁾ (continued)

 $V_{+} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	OITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Dynamic				-1					
Turn-on time,		V - V	$C_1 = 35 pF$,	25°C	5 V	5		20.5	
IN or OE	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 17	Full	1.65 V to 1.95 V	4.5		21	ns
Turn-off time.		V - V	C _L = 35 pF,	25°C	5 V	7	16.5	27.5	
IN or OE	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 17	Full	1.65 V to 1.95 V	5		30	ns
Make-before-		V - V	$C_1 = 35 pF,$	25°C	5 V	4	8.3	15	
break time	t_{MBB}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 18	Full	1.65 V to 1.95 V	4		16	ns
Charge injection	$Q_{\mathbb{C}}$	$V_{GEN} = 0,$ $R_{GEN} = 0,$	$C_L = 1 \text{ nF},$ See Figure 22	25°C	1.8 V		5		pC
NC, NO OFF capacitance	$\begin{matrix} C_{NC(OFF)}, \\ C_{NO(OFF)} \end{matrix}$	V_{NC} or $V_{NO} = V_{+}$ or GND,	Switch OFF, See Figure 16	25°C	1.8 V		19		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND,	Switch ON, See Figure 16	25°C	1.8 V		57		pF
COM OFF capacitance	C _{COM(OFF)}	V _{COM} = V ₊ or GND,	Switch ON, See Figure 16	25°C	1.8 V		36		pF
COM ON capacitance	C _{COM(ON)}	$V_{COM} = V_{+} \text{ or GND},$	Switch ON, See Figure 16	25°C	1.8 V		57		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	1.8 V		2.0		pF
Bandwidth	BW	$R_L = 50 \Omega$,	Switch ON, See Figure 19	25°C	1.8 V		100		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch OFF, See Figure 20	25°C	1.8 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch ON, See Figure 21	25°C	1.8 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	1.8 V		0.060		%
Supply									
Positive supply current	I ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	1.95 V		0.001	0.05	μΑ







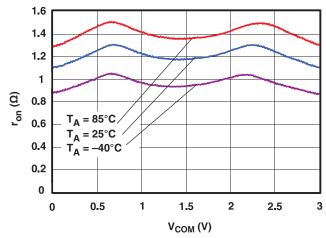
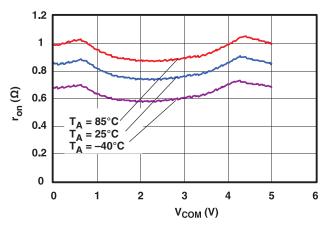


Figure 1. $r_{\rm on}$ vs $V_{\rm COM}$

Figure 2. r_{on} vs V_{COM} ($V_{+} = 3 V$)



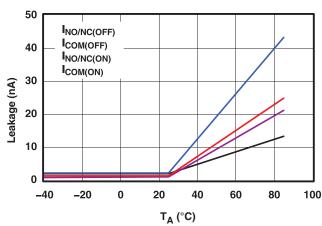
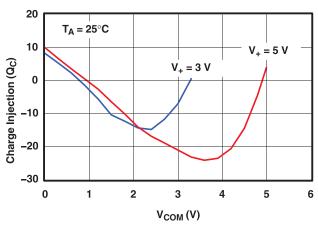


Figure 3. r_{on} vs V_{COM} ($V_{+} = 5 V$)

Figure 4. Leakage Current vs Temperature $(V_+ = 5.5 \text{ V})$



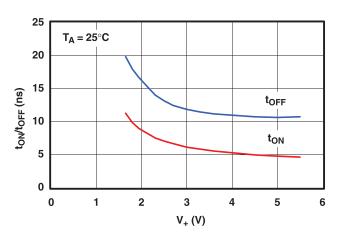
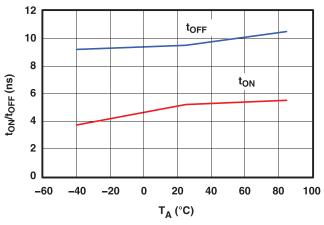


Figure 5. Charge Injection (Q_C) vs V_{COM}

Figure 6. t_{ON} and t_{OFF} vs Supply Voltage







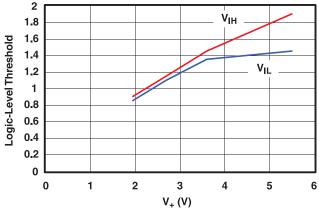
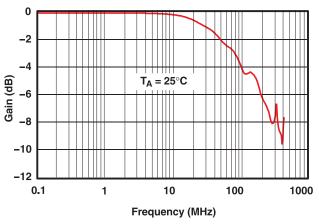


Figure 7. t_{ON} and t_{OFF} vs Temperature (V₊ = 5 V)

Figure 8. Logic-Level Threshold vs V₊



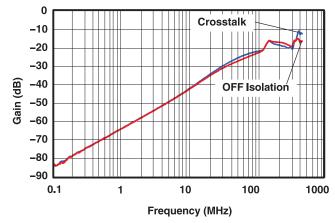
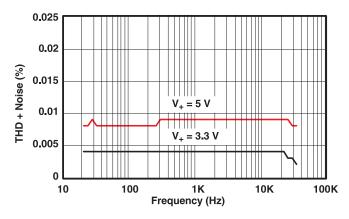


Figure 9. Bandwidth $(V_+ = 5 V)$

Figure 10. OFF Isolation and Crosstalk ($V_{+} = 5 \text{ V}$)



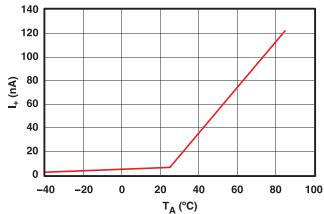


Figure 11. Total Harmonic Distortion (THD) vs Frequency

Figure 12. Power Supply Current vs Temperature
(V. = 5 V)



PIN DESCRIPTION

PIN NO.	NAME	DESCRIPTION
1	COM	Common
2	EN	Enable control input
3	GND	Digital ground
4	GND	Digital ground
5	IN	Digital control to connect the COM to NO or NC
6	NO	Normally open
7	NC	Normally closed
8	V ₊	Power supply

PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
V _{COM}	Voltage at COM
V _{NC}	Voltage at NC
V_{NO}	Voltage at NO
r _{on}	Resistance between COM and NC or COM and NO ports when the channel is ON
Δr_{on}	Difference of ron between channels in a specific device
r _{on(flat)}	Difference between the maximum and minimum value of ron in a channel over the specified range of conditions
I _{NC(OFF)}	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state
I _{NO(OFF)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state
I _{NC(ON)}	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open
I _{NO(ON)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open
I _{COM(ON)}	Leakage current measured at the COM port, with the corresponding channel (COM to NO or COM to NC) in the ON state and the output (NC or NO) open
V _{IH}	Minimum input voltage for logic high for the control input (IN)
V _{IL}	Maximum input voltage for logic low for the control input (IN)
VI	Voltage at the control input (IN)
I _{IH} , I _{IL}	Leakage current measured at the control input (IN)
t _{ON}	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON.
t _{OFF}	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFF.
t _{BBM}	Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state.
Q _C	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_{COM}$, C_L is the load capacitance and ΔV_{COM} is the change in analog output voltage.
$C_{NC(OFF)}$	Capacitance at the NC port when the corresponding channel (NC to COM) is OFF
$C_{NO(OFF)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is OFF
C _{NC(ON)}	Capacitance at the NC port when the corresponding channel (NC to COM) is ON
C _{NO(ON)}	Capacitance at the NO port when the corresponding channel (NO to COM) is ON
C _{COM(ON)}	Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON
C_{l}	Capacitance of control input (IN)
O _{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state.
X _{TALK}	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB.
BW	Bandwidth of the switch. This is the frequency where the gain of an ON channel is –3 dB below the DC gain.
THD	Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of fundamental harmonic.
	•

Submit Documentation Feedback

Copyright © 2005–2012, Texas Instruments Incorporated



PARAMETER DESCRIPTION (continued)

SYMBOL	DESCRIPTION
I ₊	Static power-supply current with the control (IN) pin at V ₊ or GND

PARAMETER MEASUREMENT INFORMATION

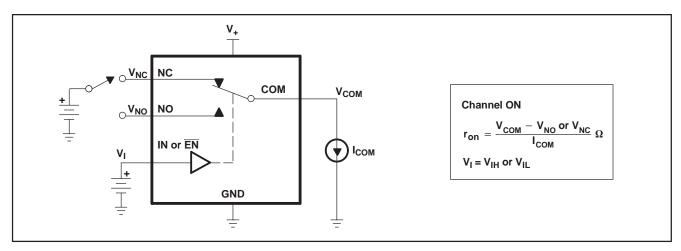


Figure 13. ON-State Resistance (ron)

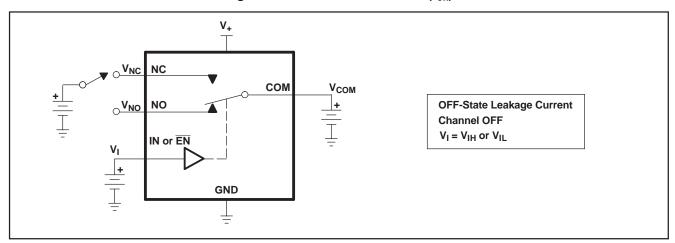


Figure 14. OFF-State Leakage Current ($I_{NC(OFF)}$, $I_{NO(OFF)}$, $I_{NO(PWROFF)}$, $I_{COM(PWROFF)}$)



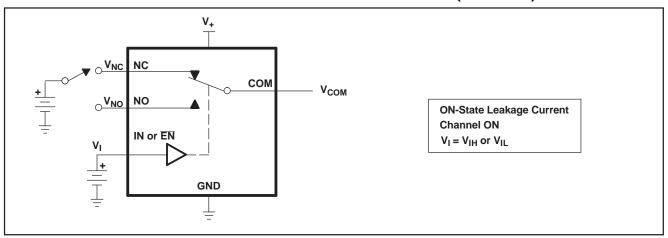


Figure 15. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NC(ON)}$, $I_{NO(ON)}$)

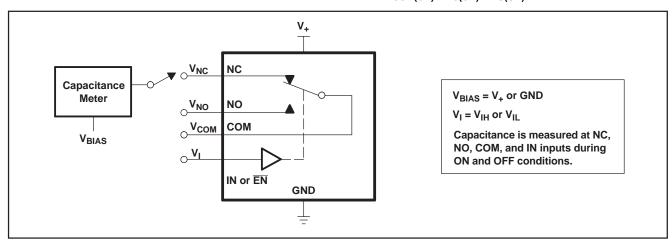
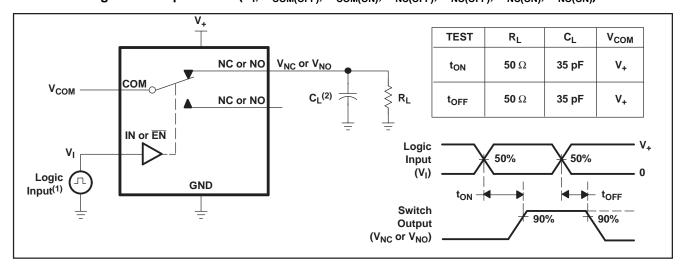


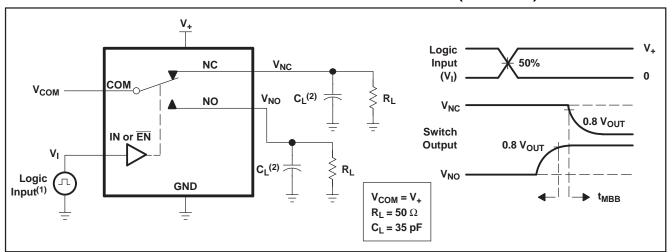
Figure 16. Capacitance (C_I, C_{COM(OFF)}, C_{COM(ON)}, C_{NC(OFF)}, C_{NO(OFF)}, C_{NC(ON)}, C_{NO(ON)})



- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.
- $^{\rm (2)}$ $\rm \,C_{L}$ includes probe and jig capacitance.

Figure 17. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})





- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r < 5 ns. t_f < 5 ns.
- (2) C_L includes probe and jig capacitance.

Figure 18. Make-Before-Break Time (t_{MBB})

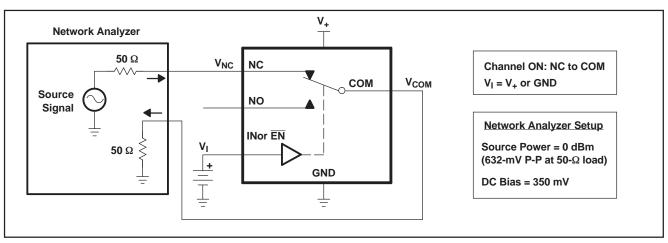


Figure 19. Bandwidth (BW)

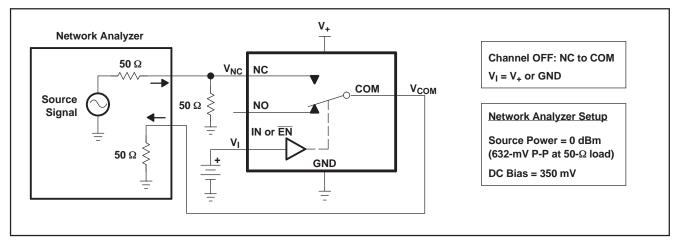


Figure 20. OFF Isolation (O_{ISO})



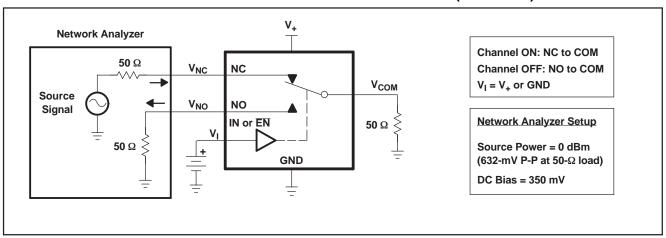
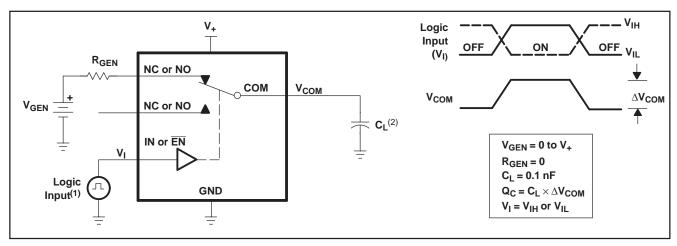


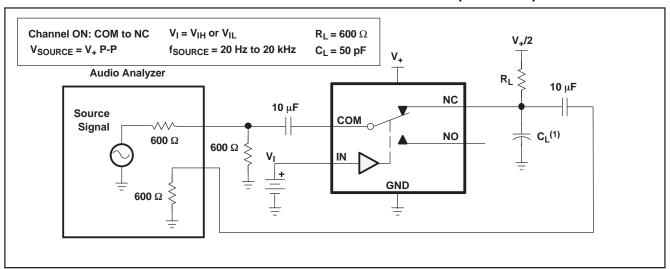
Figure 21. Crosstalk (X_{TALK})



- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.
- (2) C_L includes probe and jig capacitance.

Figure 22. Charge Injection (Q_C)





 $^{^{(1)}}$ C_L includes probe and jig capacitance.

Figure 23. Total Harmonic Distortion (THD)



REVISION HISTORY

Ch	nanges from Revision B (May 2009) to Revision C	Page
•	Changed ORDERING INFORMATION Table.	

www.ti.com 30-Aug-2021

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A3154DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(CF, JCFQ, JCFR) JZ	Samples
TS5A3154DCURE6	PREVIEW	VSSOP	DCU	8	3000	TBD	Call TI	Call TI	-40 to 85		
TS5A3154DCURG4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	JCFR	Samples
TS5A3154YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	JXN	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and



PACKAGE OPTION ADDENDUM

www.ti.com 30-Aug-2021

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 20-Mar-2024

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A3154DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
TS5A3154DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
TS5A3154DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
TS5A3154YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1



www.ti.com 20-Mar-2024



*All dimensions are nominal

7 till dillitoriolorio di o riorriiridi							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A3154DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
TS5A3154DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
TS5A3154DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
TS5A3154YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0



SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-187 variation CA.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.





DIE SIZE BALL GRID ARRAY



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2024, Texas Instruments Incorporated